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Manufacturers of World Class Discrete Semiconductors

Data Sheet

1N5817
1N5818
1N5819

SCHOTTKY BARRIER RECTIFIER

JEDEC DO-41 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 1N5817 Series types are Schottky Barrier Rectifiers mounted in an axial lead epoxy case using a metal to silicon junction to yield low forward voltage drop and instantaneous reverse recovery times.

MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

	SYMBOL	1N5817	1N5818	1N5819	UNIT
Peak Repetitive Reverse Voltage	V_{RRM}	20	30	40	V
DC Blocking Voltage	V_R	20	30	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Forward Surge Current (T_L=100°C)	I_O		1.0		A
Peak Forward Surge Current	I_{FSM}		25		A
Operating and Storage Junction Temperature	T_J, T_{STG}		-65 TO +150		°C

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	1N5817 MIN	1N5817 MAX	1N5818 MIN	1N5818 MAX	1N5819 MIN	1N5819 MAX	UNIT
I_R	V_R=V_{RRM}		1.0		1.0		1.0	mA
I_R	V_R=V_{RRM}, T_A=100°C		10		10		10	mA
V_F	I_F=0.1A		0.320		0.330		0.340	V
V_F	I_F=1.0A		0.450		0.550		0.600	V
V_F	I_F=3.1A		0.750		0.875		0.900	V

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